

N-Channel Power MOSFET

60V, 38A, $17m\Omega$

FEATURES

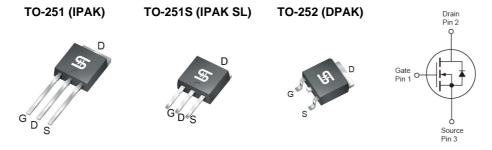
- 100% avalanche tested
- Suitable for 5V drive applications
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		60	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	17	mΩ	
	V _{GS} =4.5V	20		
Q_g		15	nC	

APPLICATION

- SMPS Synchronous Rectification
- Networking DC-DC Power System





Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	I _D	38	Α	
	T _C = 100°C		24		
Pulsed Drain Current (Note 2)		I _{DM}	152	Α	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	20	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	20	Α	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	46	W	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.7	°C/W	
Junction to Ambient Thermal Resistance	R _{OJA}	62	°C/W	

Notes: R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{eJA} is guaranteed by design while R_{eCA} is determined by the user's board design. R_{eJA} shown below for single device operation on FR-4 PCB in still air



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1.2	1.7	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current V_{DS}	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	μΑ
	$V_{DS} = 48V, V_{GS} = 0V,$ $T_{J} = 125^{\circ}C$				10	
	$V_{GS} = 10V, I_D = 20A$			15	17	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$	$R_{DS(ON)}$		17.5	20	
Dynamic (Note 5)						
Total Gate Charge		Qg		15		
Gate-Source Charge	$V_{DS} = 30V, I_{D} = 10A,$	Q_gs		5.5		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		5		
Input Capacitance		C _{iss}		900		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		130		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		90		
Gate Resistance	F = 1MHz, open drain	R_g		2.2		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		8.6		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$	t _r		24.2		
Turn-Off Delay Time	$R_G = 6\Omega$, $I_D = 1A$	t _{d(off)}		32.3		ns
Turn-Off Fall Time		t _f		7.9		
Source-Drain Diode (Note 4)						
Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}			1	V
Reverse Recovery Time	V _{GS} = 0V, I _S = 10A	t _{rr}		18		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		10		nC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 0.1 mH, $I_{AS} = 20 A$, $V_{DD} = 50 V$, $R_G = 25 \Omega$, Starting $T_J = 25 ^{\circ} C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM170N06CP ROG	TO-252(DPAK)	2,500pcs / 13" Reel
TSM170N06CH C5G	TO-251(IPAK)	75pcs / Tube
TSM170N06CH X0G	TO-251S(IPAK SL)	75pcs / Tube

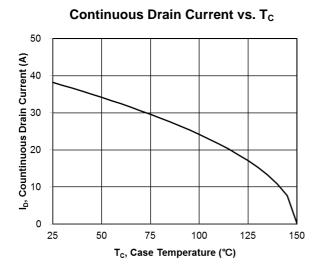
Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Gate Charge

10

V_{DS}=30V
ID=10A

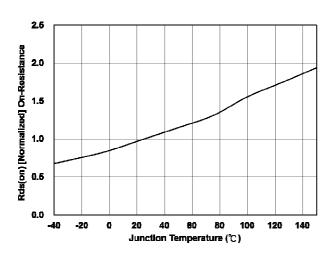
10

V_{DS}=30V
ID=10A

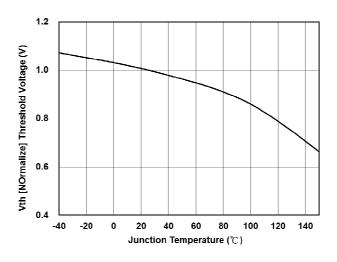
2

Q_g, Total Gate Charge (nC)

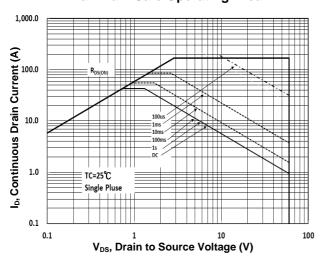
On-Resistance vs. Junction Temperature



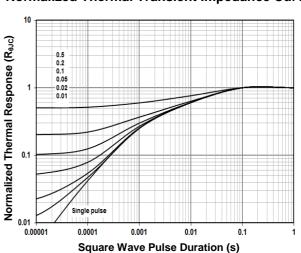
Threshold Voltage vs. Junction Temperature



Maximum Safe Operating Area

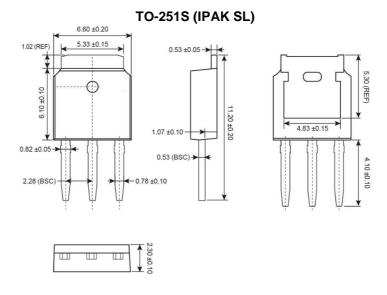


Normalized Thermal Transient Impedance Curve

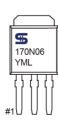




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

 \mathbf{O} =Jan \mathbf{P} =Feb \mathbf{Q} =Mar \mathbf{R} =Apr

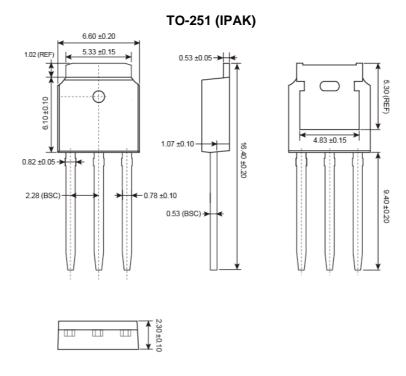
 $\label{eq:Sample_S} \textbf{S} \ = \!\!\! \text{May} \quad \textbf{T} \ = \!\!\!\! \text{Jun} \quad \textbf{U} \ = \!\!\!\!\! \text{Jul} \quad \textbf{V} \ = \!\!\!\!\! \text{Aug}$

W =Sep X =Oct Y =Nov Z =Dec

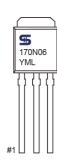
L = Lot Code (1~9, A~Z)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



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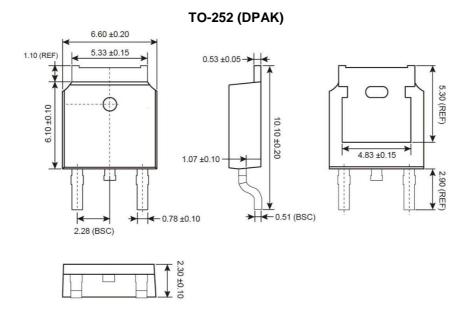
S =May T =Jun U =Jul V =Aug

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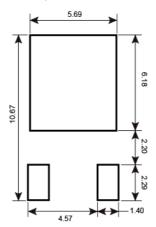
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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



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 $\textbf{S} \hspace{0.1cm} = \hspace{-0.1cm} \text{May} \hspace{0.1cm} \textbf{T} \hspace{0.1cm} = \hspace{-0.1cm} \text{Jun} \hspace{0.1cm} \textbf{U} \hspace{0.1cm} = \hspace{-0.1cm} \text{Jul} \hspace{0.1cm} \textbf{V} \hspace{0.1cm} = \hspace{-0.1cm} \text{Aug}$

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